

HALOGEN FREE



Vishay Siliconix

P-Channel 20 V (D-S) MOSFET

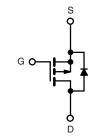
PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)						
- 20	0.0205 at $V_{GS} = -4.5 \text{ V}$	- 12 ^a							
	0.027 at V _{GS} = - 2.5 V	- 12 ^a	24.5 nC						
	0.036 at V _{GS} = - 1.8 V	- 12 ^a	24.5 110						
	0.060 at V _{GS} = - 1.5 V	- 4							

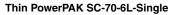
FEATURES

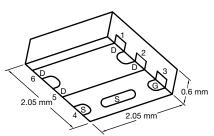
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Ultra-Thin 0.6 mm height
 - Low On-Resistance
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

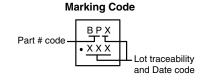
APPLICATIONS

- Load Switch and Charger Switch for Portable Devices
- DC/DC Converter









Ordering Information: SiA429DJT-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$S (T_A = 25 ^{\circ}C, \text{ unle})$	ss otherwise not	ed)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	- 20	v	
Gate-Source Voltage		V_{GS}	± 8		
	T _C = 25 °C		- 12 ^a		
Continuous Prain Current (T = 150 °C)	T _C = 70 °C		- 12 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	- 10.6 ^{b, c}		
	T _A = 70 °C		- 8.5 ^{b, c}	A	
Pulsed Drain Current (t = 300 μs)	•	I _{DM}	- 30		
Continuous Source-Drain Diode Current	T _C = 25 °C	ı	- 12 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	- 2.9 ^{b, c}		
	T _C = 25 °C		19		
Maximum Power Discipation	T _C = 70 °C	ь	12	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	VV	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperatur	e) ^{d, e}		260		

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5					

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)									
Parameter	Symbol	Symbol Test Conditions			Max.	Unit			
Static									
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 12		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η – 200 μΛ		2.7					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.4		- 1	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 100	nA			
Zero Gate Voltage Drain Current	lana	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ			
Zero Gate Voltage Diain Current	IDSS	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α			
		V _{GS} = - 4.5 V, I _D = - 6 A		0.0170	0.0205				
		$V_{GS} = -2.5 \text{ V}, I_D = -2 \text{ A}$		0.022	0.027	Ω			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 2 A		0.029	0.036				
		V _{GS} = - 1.5 V, I _D = - 1 A		0.038	0.060	7			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 6 A		30		S			
Dynamic ^b									
Input Capacitance	C _{iss}			1750		pF			
Output Capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		270					
Reverse Transfer Capacitance	C _{rss}			240					
Tatal Cata Chausa	Qg	V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 10 A		41	62	nC			
Total Gate Charge				24.5	37				
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -10 \text{ A}$		2.4					
Gate-Drain Charge	Q_{gd}			6.7					
Gate Resistance	R_{g}	f = 1 MHz	1.3	6.3	13	Ω			
Turn-On Delay Time	t _{d(on)}			22	35				
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1.2 Ω		25	40				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 8.5 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		70	105				
Fall Time	t _f			25	40				
Turn-On Delay Time	t _{d(on)}			10	15	ns			
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 1.2 \Omega$		10	15	- - -			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -8.5 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$		80	120				
Fall Time	t _f			25	40				
Drain-Source Body Diode Characterist	ics					L			
Continuous Source-Drain Diode Current I _S		T _C = 25 °C			- 12	^			
Pulse Diode Forward Current	I _{SM}				- 30	A			
Body Diode Voltage	V_{SD}	I _S = - 8.5 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t _{rr}			35	60	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	0 E A dl/d+ 100 A/ T 05 00		18	30	nC			
Reverse Recovery Fall Time	t _a	$I_F = -8.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		13					
Reverse Recovery Rise Time	t _b			22		ns			

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

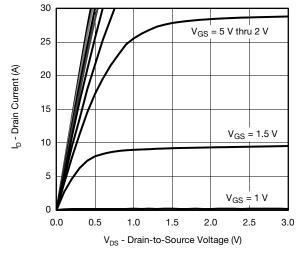
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

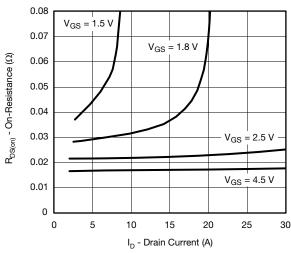


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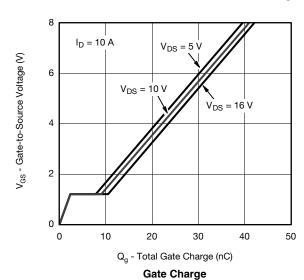
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

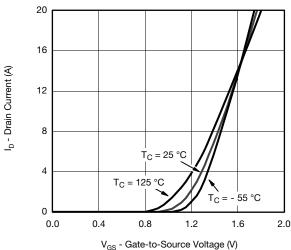


Output Characteristics

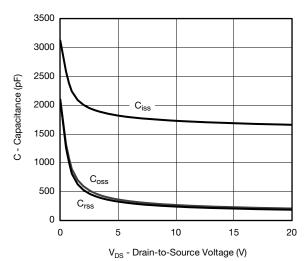


On-Resistance vs. Drain Current and Gate Voltage

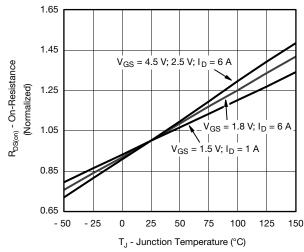




Transfer Characteristics



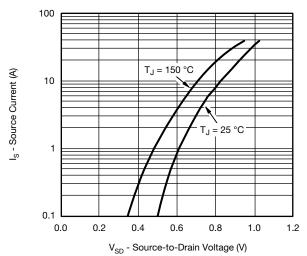
Capacitance



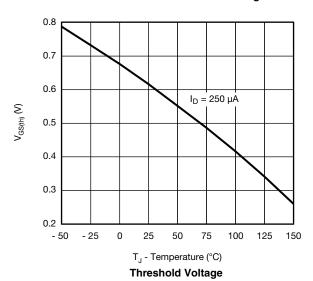
On-Resistance vs. Junction Temperature

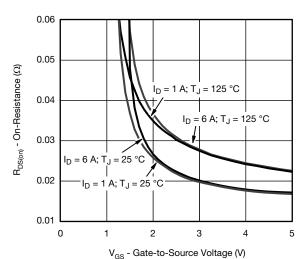
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

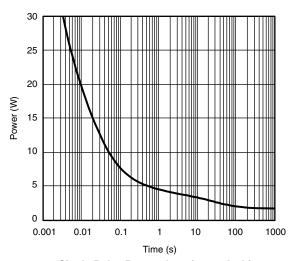


Soure-Drain Diode Forward Voltage

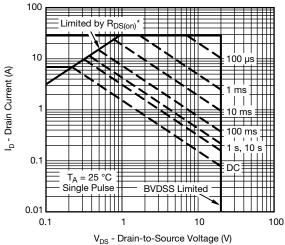




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



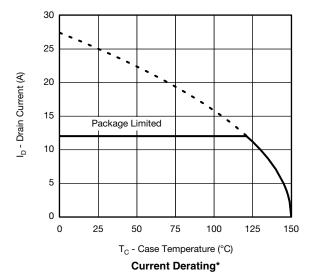
 * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

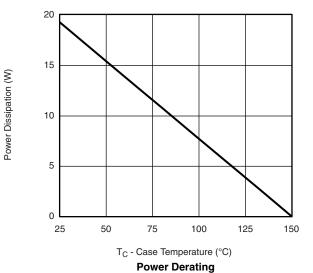
Safe Operating Area, Junction-to-Ambient



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

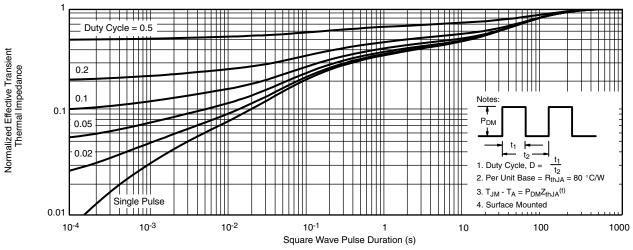




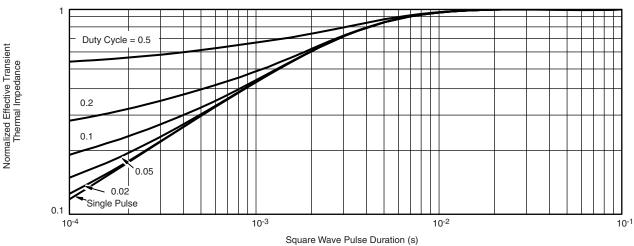
 $^{^*}$ The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

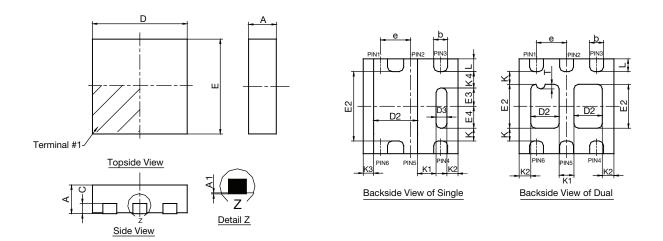
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67038





www.vishay.com

Case Outline for PowerPAK® SC70T



	SINGLE PAD							DUAL PAD				
DIM.	MILLIMETERS			INCHES		MILLIMETERS		INCHES				
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.525	0.60	0.65	0.0206	0.024	0.026	0.525	0.60	0.65	0.0206	0.024	0.026
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D2	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D3	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E2	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E3	0.345	0.395	0.445	0.014	0.016	0.018						
E4	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC		0.026 BSC			0.65 BSC			0.026 BSC		
K		0.275 TYP. 0.011 TYP.		0.275 TYP.			0.011 TYP.					
K1		0.400 TYP. 0.016 TYP.		0.320 TYP.			0.013 TYP.					
K2		0.240 TYP. 0.009 TYP.		0.252 TYP.		0.010 TYP.						
K3		0.225 TYP.		0.009 TYP.								
K4		0.355 TYP.		0.014 TYP.								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C12-0160-Rev. B. 05-Mar-12												

DWG: 5994

DWG. 5994

Notes

- 1. All dimensions are in millimeter. Millimeters will govern.
- 2. Package outline exculsive of mold flash and metal burr.
- 3. Package outline inclusive of plating



Legal Disclaimer Notice

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